

DB4J406K0R
 Silicon epitaxial planar type

Unit: mm

For high speed switching circuits

■ Features

- Small reverse current IR
- Short reverse recovery time trr
- Halogen-free / RoHS compliant
 (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: 4B

■ Basic Part Number :
 Dual DB2J406 (Parallel)

■ Packaging

Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)

- 1. Anode1
- 2. Anode2
- 3. Cathode2
- 4. Cathode1

Panasonic JEITA SMini4-F3-B SC-113BB

■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Repetitive peak reverse voltage	VRRM	40	V
	IF	100	
		75	
Non-repetitive peak forward surge current	IFSM	1	
Junction temperature	Tj	0.75	°C
Operating ambient temperature	Topr	-40 to +85	°C
Storage temperature	Tstg	-55 to +125	°C

Internal Connection

Note: *1 Value of each diode in double used.

*2 The peak-to-peak value in one cycle of 50 Hz sine wave (non-repetitive)